

**SCHOTTKY DIODES KDS 2128I.**  
PRELIMINARY



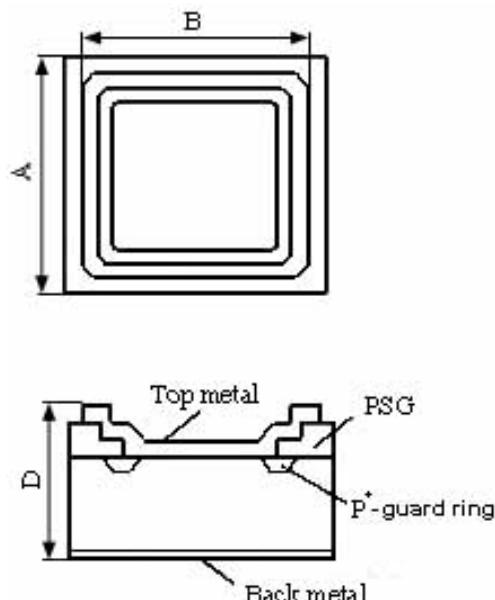
Rev.1. Feb. 2010



**VSP-MIKRON**

**1A/25V. Die Size-51mil.**

Electrical Characteristics	Symbol	Unit	Spec. limit	Die Sort
Breakdown Voltage @ $I_R=10\text{mA}$	$V_{BR}$	V	28	30
Average Rectified Forward Current	$I_{F(AV)}$	A	1,0	-
DC Forward Voltage @ $25^\circ\text{C}$ , $I_F=1,0\text{A}$	$V_F$	V	0,33	0,32
Maximum Reverse Current @ $25^\circ\text{C}$ , $V_R=25\text{V}$ $25^\circ\text{C}$ , $V_R=28\text{V}$ $100^\circ\text{C}$ , $V_R=25\text{V}$	$I_R$	mA	0,6 - 50,0	0,5 0,6 45,0
Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	$I_{FSM}$	A	60	-
Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$ , $f=1\text{kHz.}$ , $T_J<125^\circ\text{C.}$	$I_{RRM}$	A	2,0	
Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact.	ESD	kV	$\pm 8$ (contact)	
Voltage Rate of Change	$dV/dt$	V/ $\mu\text{S}$	10.000	
Operating Junction Temperature	$T_J$	$^\circ\text{C}$	125	



DIM	ITEM	$\mu\text{m}$
$A_x$ $A_y$	Wafer Form Die Size	1300 1300
$B_x$ $B_y$	Top Metal Size	1112 1112
D	Thickness	300max.
Scribe line Width		80

*Top metal:* a) **Al** – for Wire Bonding;  
b) **Al-Ni-Ag** – for Soldering.

*Backside metal:* **Ti-Ni-Ag**.